

Rev.F Apr.-2017

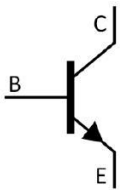
SOT-23

NPN

Silicon NPN transistor in a SOT-23 Plastic Package.

Large current capacity and wide ASO.

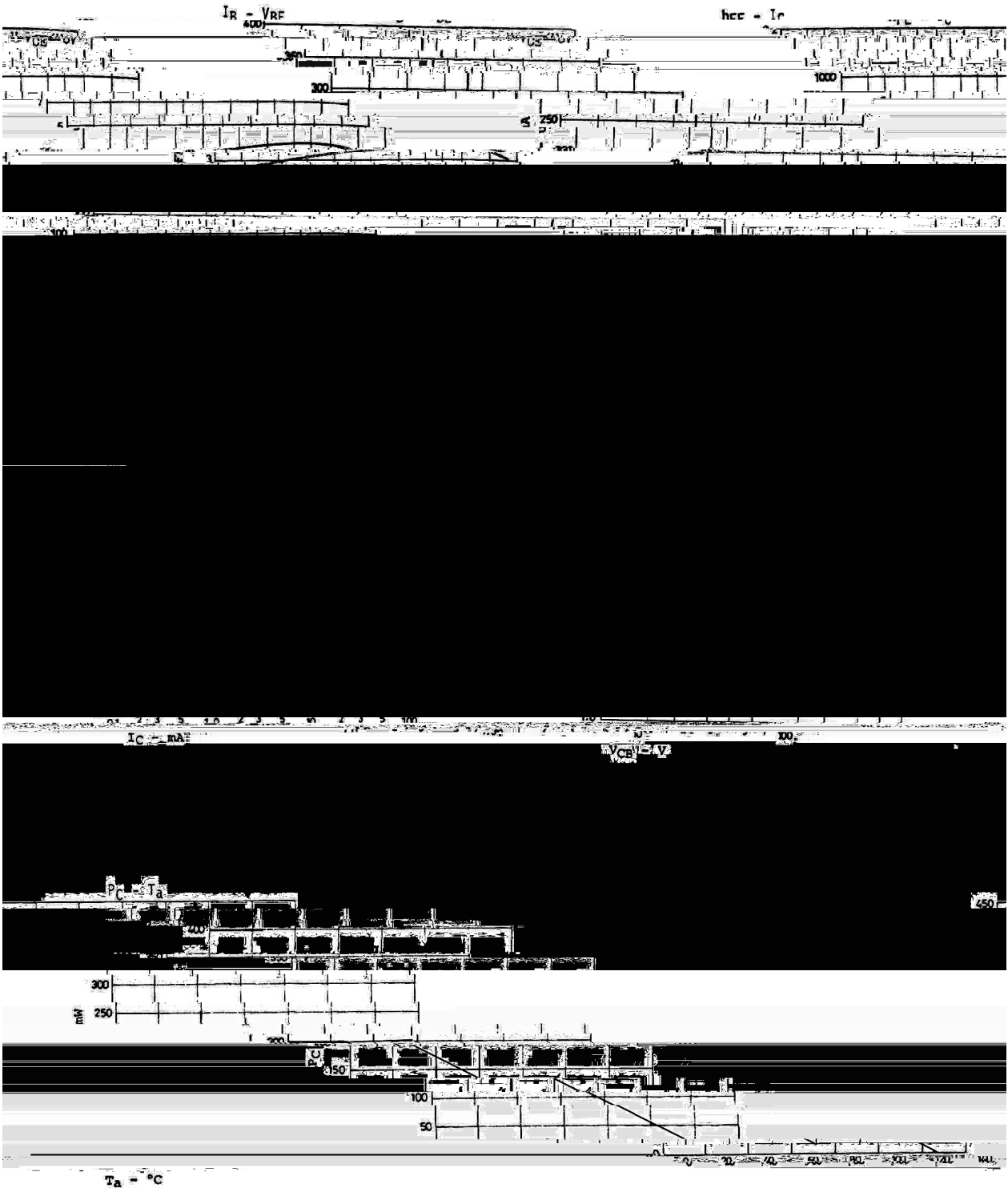
Small signal general purpose amplifier applications.

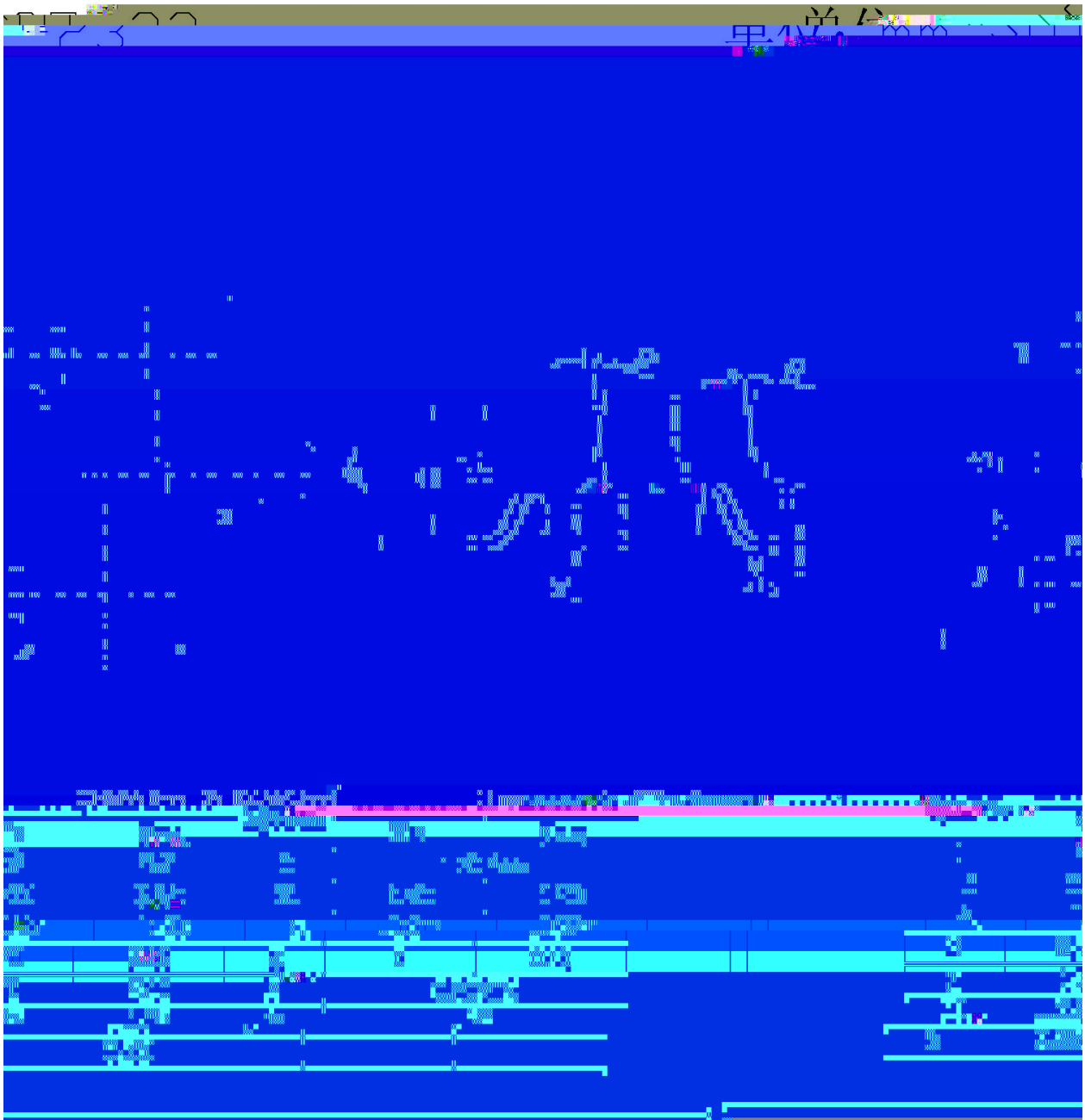


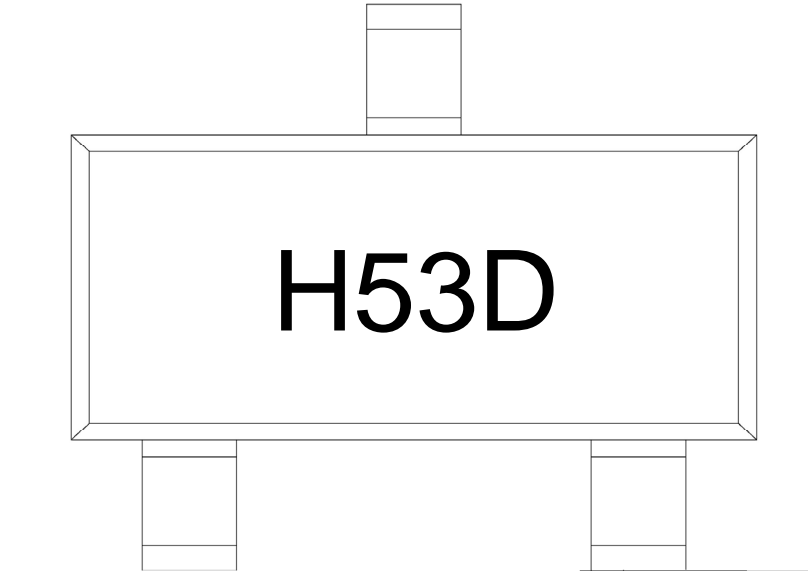
PIN1

Parameter		Symbol	Rating	Unit
Collector to Base Voltage	2SC536M 2SC536KM	V_{CBO}	40 55	V
Collector to Emitter Voltage	2SC536M 2SC536KM	V_{CEO}	30 50	V
Emitter to Base Voltage		V_{EBO}	5.0	V
Collector Current		I_C	100	mA
Collector Current(pulse)		I_{CP}	300	mA
Collector Power Dissipation		P_C	250	mW
Junction Temperature		T_j	150	
Storage Temperature Range		T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=35V$ $I_E=0$			1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=4.0V$ $I_C=0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=1.0mA$	60		960	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50mA$ $I_B=5.0mA$			0.5	V
Transition Frequency	f_T	$V_{CE}=6.0V$ $I_C=1.0mA$		100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=6.0V$ $I_E=0$ $f=1.0MHz$		3.5		pF
Collector- Base Time Constant	C_{C-rbb}	$V_{CB}=6.0V$ $I_C=1.0mA$ $f=31.9MHz$		250		pS







H

53

D h_{FE}

Note:

H Company Code

53 Product Type Code

D h_{FE} Classifications Symbol Code

